

DERWENT- 2002-749096
ACC-NO:

DERWENT- 200281
WEEK:

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TITLE: Method for forming silicon carbon nitride layer on low-k material -
preventing delamination occurring at the interface between
silicon carbon nitride layer and low-k layer

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PRIORITY-DATA: 2001TW-0100649 (January 11, 2001)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
TW 471112 A	January 1, 2002	N/A	000	H01L 021.76

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
TW 471112A	N/A	2001TW-0100649	January 11, 2001

INT-CL (IPC): H01L021/76

ABSTRACTED-PUB-NO: TW 471112A

BASIC-ABSTRACT:

NOVELTY - The present invention discloses a method for forming silicon carbon nitride layer on low dielectric constant (low-k) material which includes

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the following steps: (1) forming a first low-k dielectric layer on a semiconductor substrate, (2) forming silicon carbide layer on the first low-k dielectric layer, (3) conducting ion implantation on the silicon carbide layer to convert the silicon carbide layer into the silicon carbon nitride layer, in which the plasma ions comprise nitrogen ions, such as NH_3 or N_2 ; in which the material of the first low-k dielectric layer comprises FSG, SiLK, FLARE or nanoglass. The forming method for silicon carbide layer includes obtaining by conducting plasma enhanced chemical vapor deposition (PECVD) in an environment containing $\text{Si}(\text{CH}_3)_4$ (referred as 4MS in the industry), or $\text{SiH}(\text{CH}_3)_3$ (referred as 3MS in the industry), $\text{SiH}_2(\text{CH}_3)_2$ (referred as 2MS in the industry), $\text{SiH}_3(\text{CH}_3)$ (referred as MS in the industry).

CHOSEN- Dwg.0/1
DRAWING:

TITLE- METHOD FORMING SILICON CARBON NITRIDE LAYER LOW
TERMS: MATERIAL PREVENT DELAMINATE OCCUR INTERFACE
SILICON CARBON NITRIDE LAYER LOW LAYER

DERWENT-CLASS: L03 U11

CPI-CODES: L04-C01B; L04-C02B; L04-C12B;

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